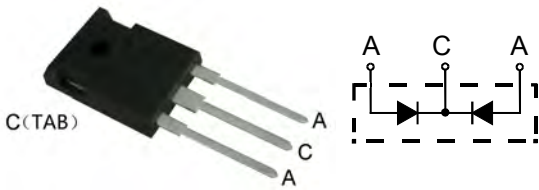


MBR30100PT thru MBR30200PT

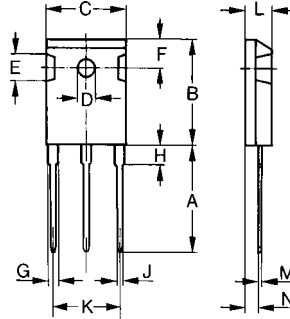
High T_{jm} Low IRRM Schottky Barrier Diodes



A=Anode, C=Cathode, TAB=Cathode

	V _{RRM} V	V _{RMS} V	V _{DC} V
MBR30100PT	100	70	100
MBR30150PT	150	105	150
MBR30200PT	200	140	200

Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Symbol	Characteristics	Maximum Ratings	Unit
I <sub(av)< sub=""></sub(av)<>	Maximum Average Forward Rectified Current @T _c =125°C	30	A
I _{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	250	A
dv/dt	Voltage Rate Of Change (Rated V _R)	10000	V/us
V _F	Maximum Forward Voltage (Note 1) I _F =15A @T _J =25°C I _F =15A @T _J =125°C I _F =30A @T _J =25°C I _F =30A @T _J =125°C	0.85 0.70 0.98 0.85	V
I _R	Maximum DC Reverse Current @T _J =25°C At Rated DC Blocking Voltage @T _J =125°C	0.05 10	mA
R _{θJC}	Typical Thermal Resistance (Note 2)	2.2	°C/W
C _J	Typical Junction Capacitance Per Element (Note 3)	700	pF
T _J	Operating Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

NOTES: 1. 300us Pulse Width, Duty Cycle 2%.
2. Thermal Resistance Junction To Case.
3. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

FEATURES

- * Metal of silicon rectifier, majority carrier conduction
- * Guard ring for transient protection
- * Low power loss, high efficiency
- * High current capability, low V_F
- * High surge capacity
- * For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- * RoHS compliant

MECHANICAL DATA

- * Case: TO-247AD molded plastic
- * Polarity: As marked on the body
- * Weight: 6 grams
- * Mounting position: Any

Sirectifier®

MBR30100PT thru MBR30200PT

High T_{jm} Low IRRM Schottky Barrier Diodes

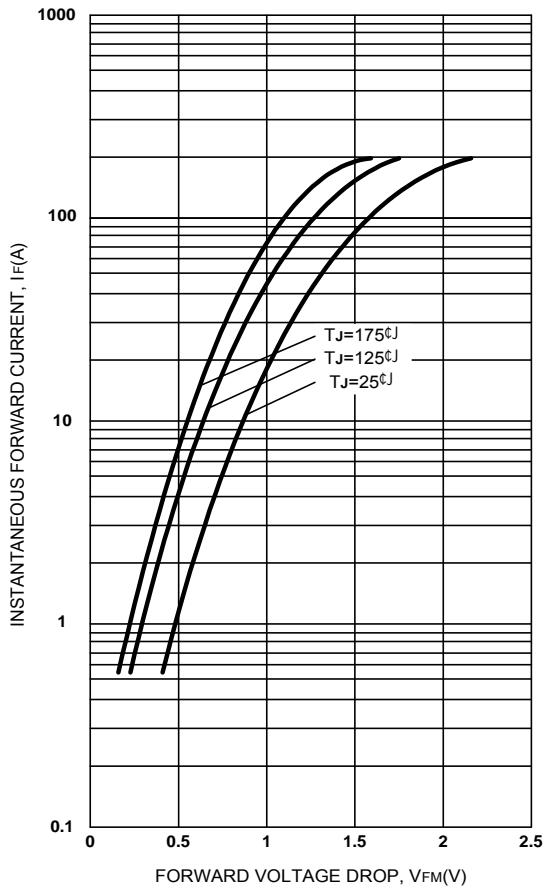


Figure 1. Max. Forward Voltage Drop Characteristics (Per Leg)

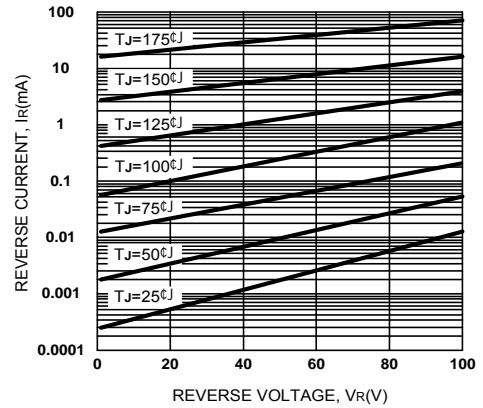


Figure 2. Typical Values Of Reverse Current Vs. Reverse Voltage (Per Leg)

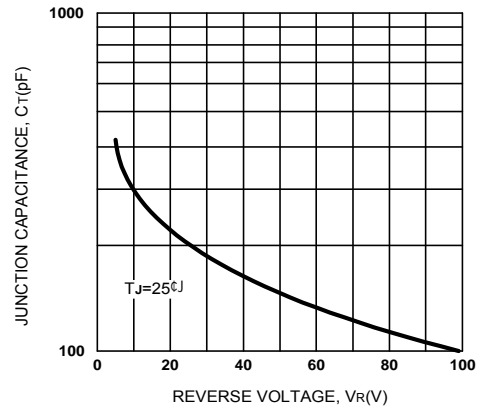


Figure 3. Typical Junction Capacitance Vs. Reverse Voltage (Per Leg)

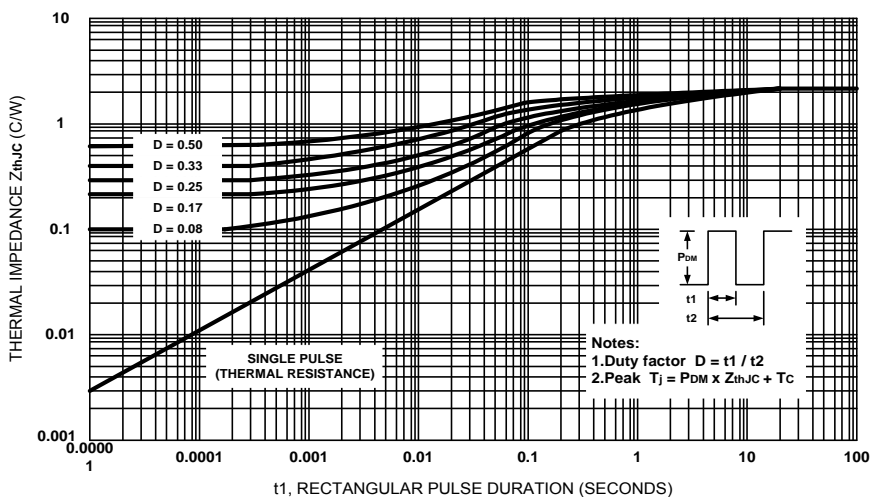


Figure 4. Max. Thermal Impedance Z_{thJC} Characteristics (Per Leg)



MBR30100PT thru MBR30200PT

High T_{jm} Low IRRM Schottky Barrier Diodes

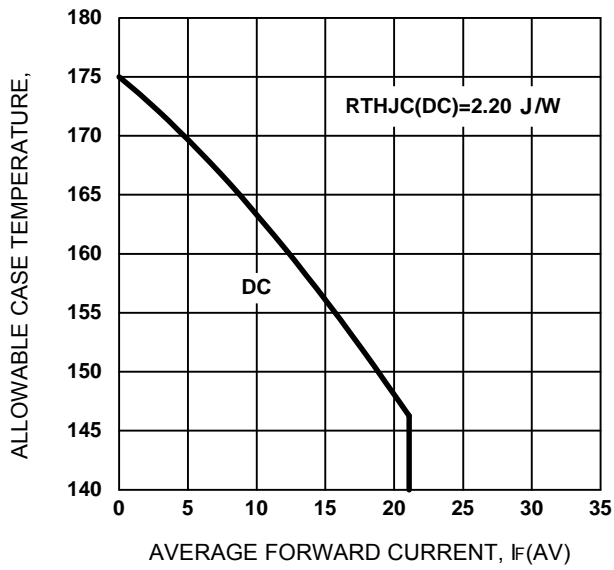


Figure 5. Max. Allowable Case Temperature Vs. Average Forward Current (Per Leg)

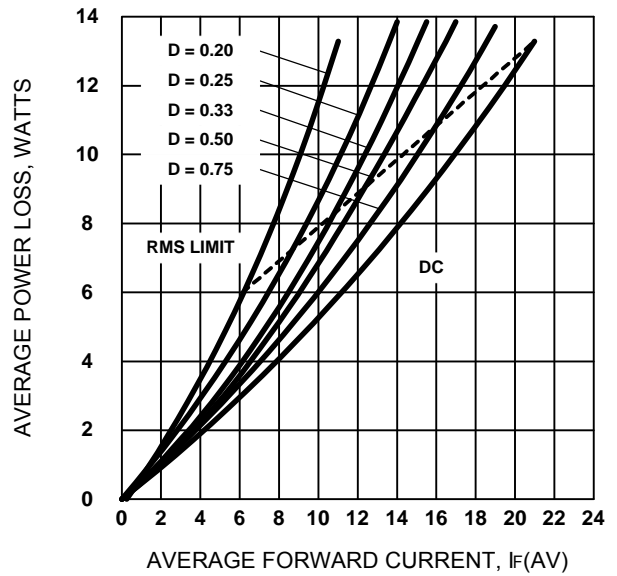


Figure 6. Forward Power Loss Characteristics (Per Leg)

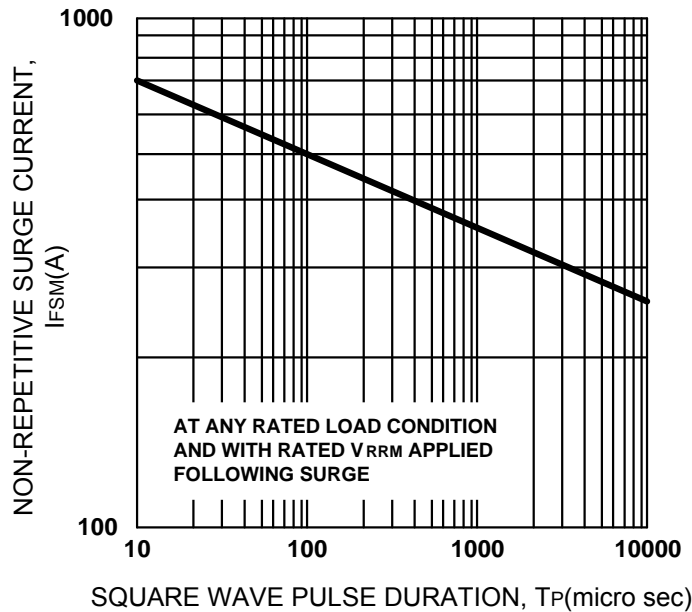


Figure 7. Max. Non-Repetitive Surge Current (Per Leg)

